

2SC1226, 2SC1226A

Silicon NPN Epitaxial Planar Type

Medium Power Amplifier

Complementary Pair with 2SA699, 2SA699A

Feature

- 5W output in complementary pair with 2SA699, 2SA699A

Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Value	Unit
Collector-base voltage	2SC1226	40	V
	2SC1226A		
Collector-emitter voltage	2SC1226	32	V
	2SC1226A	40	
Emitter-base voltage	V_{EBO}	5	V
Peak collector current	I_{CP}	3	A
Base current	I_B	0.6	A
Collector power dissipation (Tc=25°C)	P_C	10	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CBO}	$V_{CB}=20\text{ V}, I_E=0$			1	μA
	I_{CEO}	$V_{CE}=12\text{ V}, I_B=0$			100	
Emitter cutoff current	I_{EBO}	$V_{EB}=5\text{ V}, I_C=0$			100	μA
Collector-base voltage	2SC1226	$I_C=1\text{ mA}, I_E=0$	40			V
	2SC1226A		50			
Collector-emitter voltage	2SC1226	$I_C=10\text{ mA}, I_B=0$	32			V
	2SC1226A		40			
DC current gain	h_{FE}^{*1}	$V_{CE}=5\text{ V}, I_C=1\text{ A}^{*2}$	50	120	220	
Transition frequency	f_T	$V_{CE}=5\text{ V}, I_C=0.5\text{ A}^{*2}$		150		MHz
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=2\text{ A}, I_B=0.2\text{ A}^{*2}$			1.5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{ A}, I_B=0.2\text{ A}^{*2}$		0.4	1	V
Collector output capacitance	C_{ob}	$V_{CB}=5\text{ V}, I_E=0, f=1\text{ MHz}$		50		pF

*2 パルス測定

hFE Classifications

Class	P	Q	R
h_{FE}	50 ~ 100	80 ~ 160	120 ~ 220

Package Dimensions

